

2SD1819G

Silicon NPN epitaxial planar type

For general amplification

Complementary to 2SB1218G

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape pacing and the magazine pacing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	60	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Collector current	I_C	100	mA
Peak collector current	I_{CP}	200	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
SMini3-F2
- Marking Symbol: Z
- Pin Name
1: Base
2: Emitter
3: Collector

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

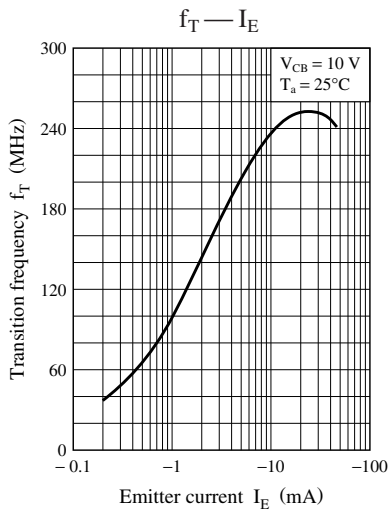
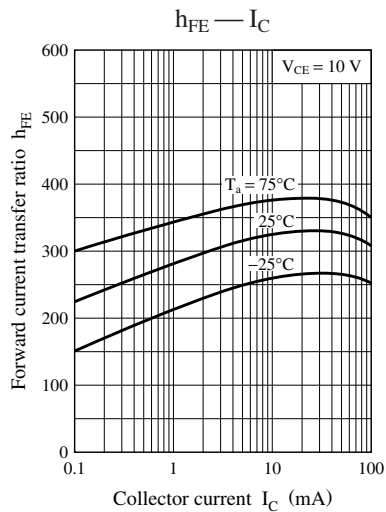
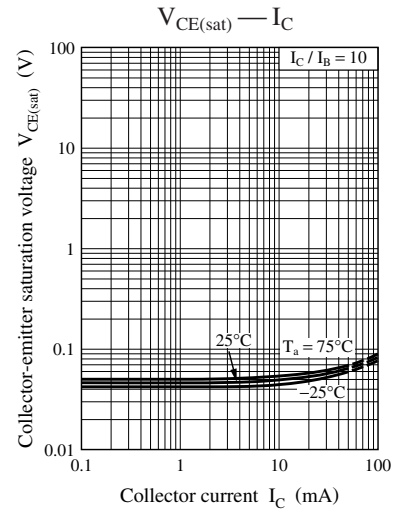
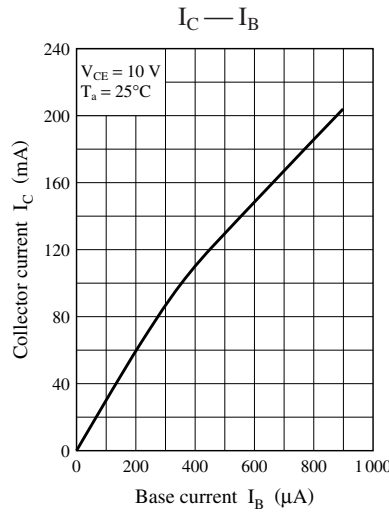
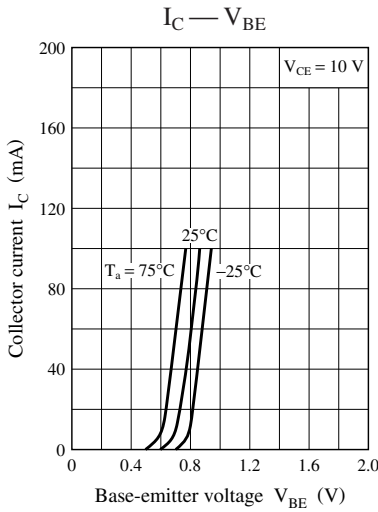
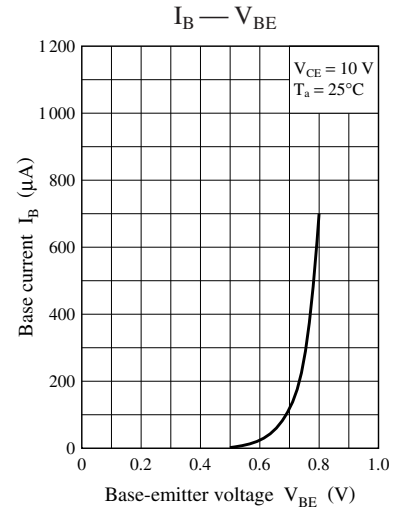
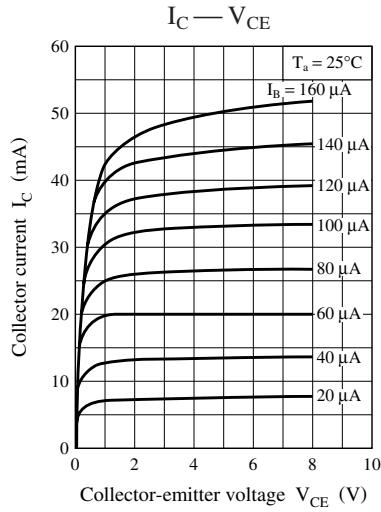
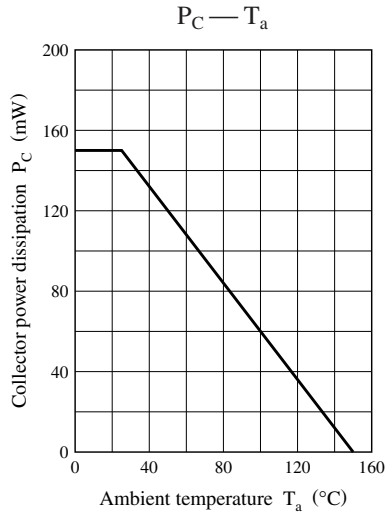
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}$, $I_E = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}$, $I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}$, $I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}$, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10 \text{ V}$, $I_B = 0$			100	μA
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = 10 \text{ V}$, $I_C = 2 \text{ mA}$	160		460	—
	h_{FE2}	$V_{CE} = 2 \text{ V}$, $I_C = 100 \text{ mA}$	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}$, $I_B = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}$, $I_E = -2 \text{ mA}$, $f = 200 \text{ MHz}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		3.5		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

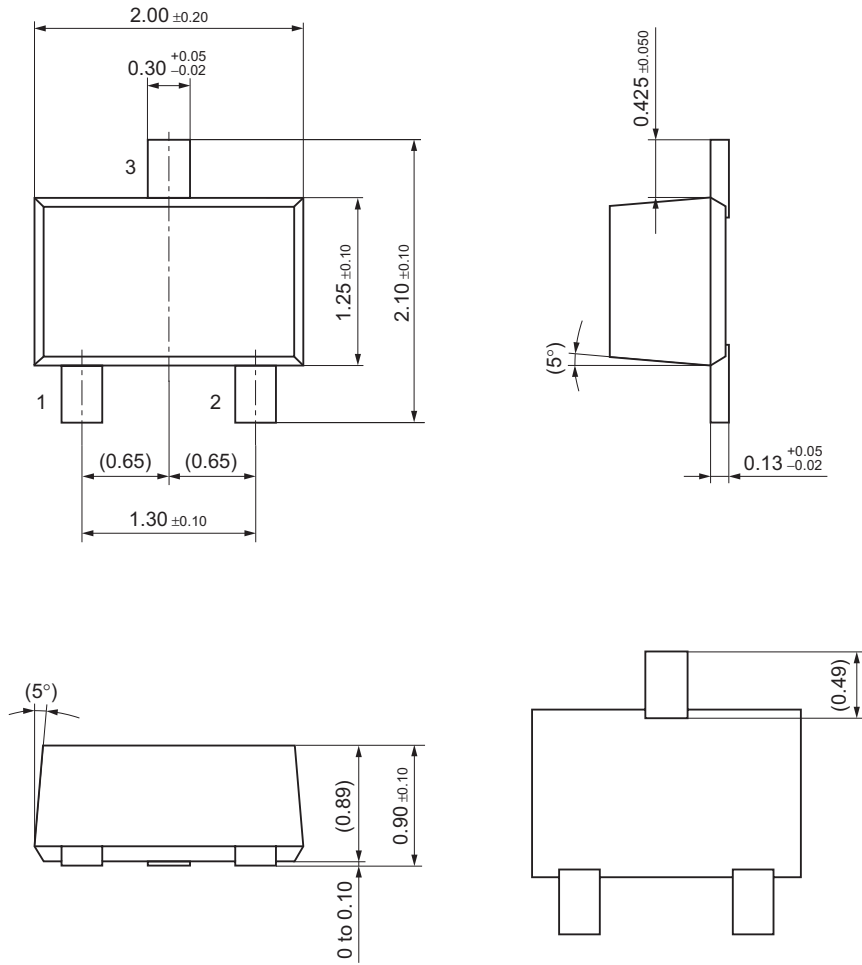
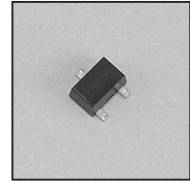
Rank	Q	R	S	No rank
h_{FE1}	160 to 260	210 to 340	290 to 460	160 to 460
Marking symbol	ZQ	ZR	ZS	Z

Product of no-rank is not classified and have no marking symbol for rank.



SMini3-F2

Unit: mm



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